MSKSEMI















ESD

TVS

TSS

MOV

GDT

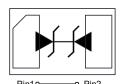
PLED

Broduct data sheet





DFN1610-2L



Marking D4N

Feature

- > 1200W Peak pulse power per line ($t_P = 8/20\mu s$)
- DFN1610-2L package
- Response time is typically < 1 ns</p>
- Protect one I/O or power line
- Low clamping Voltage
- RoHS compliant
- Transient protection for data lines to IEC 61000-4-2(ESD) ±30KV(air), ±30KV(contact); IEC 61000-4-4 (EFT) 40A (5/50ns)

Applications

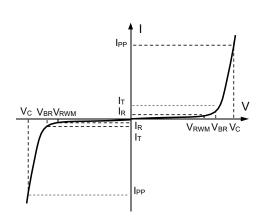
- > Cell phone handsets and accessories
- Personal digital assistants (PDA's)
- Notebooks, desktops, and servers
- Portable instrumentation
- Cordless phones
- Digital cameras
- Peripherals
- MP3 players

Mechanical Characteristics

- ➤ Lead finish:100% matte Sn(Tin)
- Mounting position: Any
- Qualified max reflow temperature:260°C
- ➤ Pure tin plating: 7 ~ 17 um
- ➤ Pin flatness:≤3mil
- Device meets MSL 3 requirements

Electronics Parameter

Symbol	Parameter	
V _{RWM}	Peak Reverse Working Voltage	
I _R	Reverse Leakage Current @ V _{RWM}	
V_{BR}	Breakdown Voltage @ I _T	
lτ	Test Current	
I _{PP}	Maximum Reverse Peak Pulse Current	
Vc	Clamping Voltage @ IPP	
P _{PP}	P _{PP} Peak Pulse Power C _J Junction Capacitance	
CJ		





Electrical characteristics per line@25℃(unless otherwise specified)

Parameter	Symbol	Conditions	Min.	Тур.	Max.	Units
Reverse Zener Voltage	Vz	I _{ZT} = 5mA		5.1		V
Reverse Working Voltage ⁽¹⁾	V _{RWM}				4.5	V
Breakdown Voltage(PIN1~PIN2)	V _{BR}	I _t =1mA	4.6	5.2	6.1	V
Reverse Leakage Current(PIN1~PIN2)	I _R	V _{RWM} =4.5V			0.2	μA
Clamping Voltage(PIN1~PIN2)	Vc	I _{PP} =20A t _P = 8/20μs		6.5	8	V
Clamping Voltage(PIN1~PIN2)	Vc	I _{PP} =45A t _P = 8/20µs		7.5	9	V
Clamping Voltage(PIN1~PIN2)	Vc	I _{PP} =90A t _P = 8/20μs		9.5	12	V
Clamping Voltage(PIN1~PIN2)	Vc	I _{PP} =130A t _P = 8/20μs		10	13	V
Junction Capacitance	C _j	V _R =0V f = 1MHz		400	500	pF

Note 1: V_{RWM} is the maximum reverse working voltage, or reverse stand-off voltage. ESD can protect signal line properly within its rated voltage. If the signal line's voltage is over V_{RWM} , ESD will change to other state.

Absolute maximum rating@25℃

Rating	Symbol	Value	Units
Peak Pulse Power (t _P = 8/20µS)	P _{pp}	1200	W
Total Device Dissipation FR-5 Board	P _D	500	mW
Lead Soldering Temperature	T∟	260 (10 sec)	°C
Operating Temperature	TJ	-55 to +150	°C
Storage Temperature	Tstg	-55 to +150	°C



Typical Characteristics

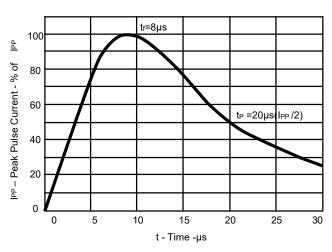


Fig 1.Pulse Waveform

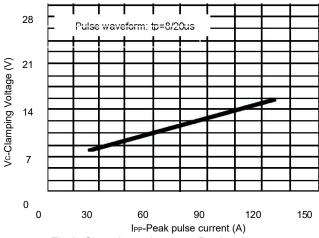


Fig 3. Clamping voltage vs. Peak pulse current

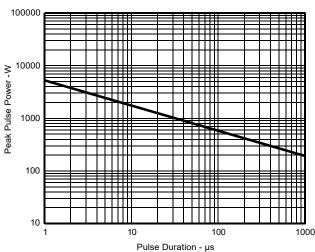


Fig 5. Non Repetitive Peak Pulse Power vs. Pulse time

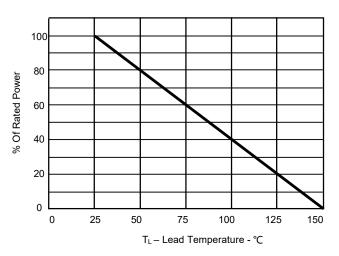
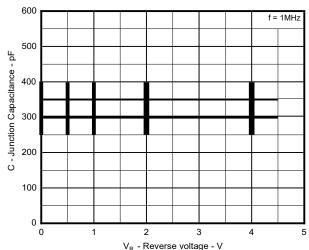


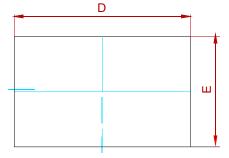
Fig 2.Power Derating Curve

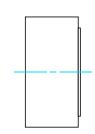


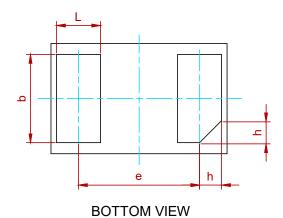
 $$V_{R}$$ - Reverse voltage - V Fig 4. Capacitance vs. Reveres voltage



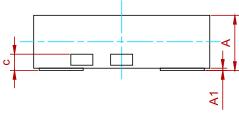
PACKAGE MECHANICAL DATA







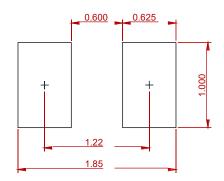
TOP VIEW



SIDE VIEW

Complete	Dimensions in Millimeters			
Symbol	Min.	Тур.	Max.	
А	0.45	0.50	0.55	
A1	0.00	0.02	0.05	
С		0.15 Ref.		
b	0.75	0.80	0.85	
L	0.35	0.40	0.45	
D	1.55	1.60	1.65	
Е	0.95	1.00	1.05	
е		1.10 BSC		
h		0.20 Ref.		

Recommend PCB Layout (Unit: mm)



Notes:

This recommended land pattern is for reference purposes only. Please consult your manufacturing group to ensure your PCB design guidelines are met.

REEL SPECIFICATION

P/N	PKG	QTY
PTVSHC2EN4V5B-MS	DFN1610-2L	3000



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